

## Low Voltage Bias Stabilizer with Enable

- Maintains Stable Bias Current in N-Type Discrete Bipolar Junction and Field Effect Transistors
- Provides Stable Bias Using a Single Component Without Use of Emitter Ballast and Bypass Components
- Operates Over a Wide Range of Supply Voltages Down to 1.8 Vdc
- Reduces Bias Current Variation Due to Temperature and Unit-to-Unit Parametric Changes
- Consumes <math><0.5\text{ mW}</math> at  $V_{CC} = 2.75\text{ V}$
- Active High Enable is CMOS Compatible

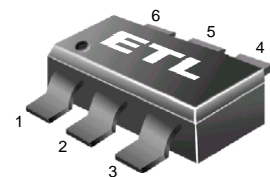
This device provides a reference voltage and acts as a DC feedback element around an external discrete, NPN BJT or N-Channel FET. It allows the external transistor to have its emitter/source directly grounded and still operate with a stable collector/drain DC current. It is primarily intended to stabilize the bias of discrete RF stages operating from a low voltage regulated supply, but can also be used to stabilize the bias current of any linear stage in order to eliminate emitter/source bypassing and achieve tighter bias regulation over temperature and unit variations. The "ENABLE" polarity nulls internal current, Enable current, and RF transistor current in "STANDBY." This device is intended to replace a circuit of three to six discrete components.

The combination of low supply voltage, low quiescent current drain, and small package make the MDC5001T1 ideal for portable communications applications such as:

- Cellular Telephones
- Pagers
- PCN/PCS Portables
- GPS Receivers
- PCMCIA RF Modems
- Cordless Phones
- Broadband and Multiband Transceivers and Other Portable Wireless Products.

### MDC5001T1

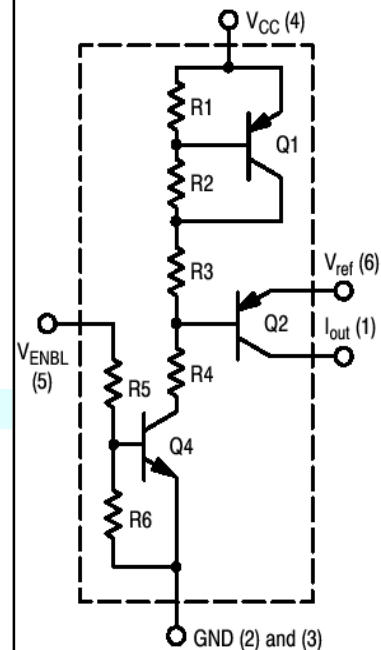
SILICON  
SMALLBLOCK™  
INTEGRATED CIRCUIT



SOT-363

CASE 419B-01 STYLE 19

### INTERNAL CIRCUIT DIAGRAM



**MAXIMUM RATINGS**

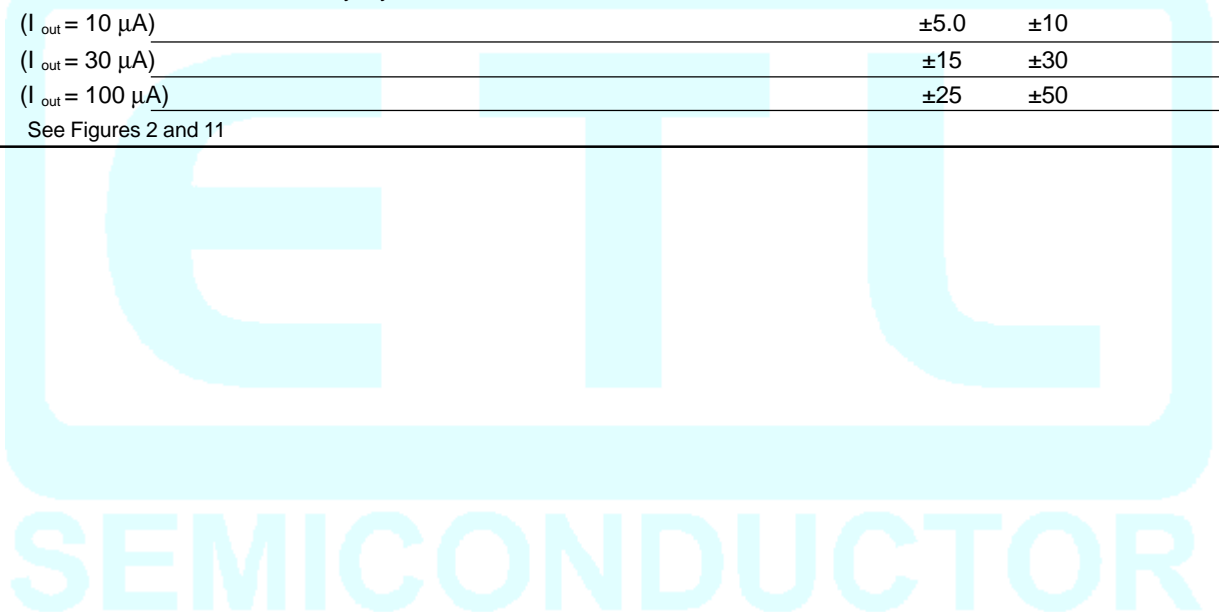
Rating	Symbol	Value	Unit
Power Supply Voltage	$V_{CC}$	15	$V_{dc}$
Ambient Operating Temperature Range	$T_A$	-40 to +85	$^{\circ}C$
Storage Temperature Range	$T_{stg}$	-65 to +150	$^{\circ}C$
Junction Temperature	$T_J$	150	$^{\circ}C$
Collector Emitter Voltage (Q2)	$V_{CEO}$	-15	V
Enable Voltage (Pin 5)	$V_{ENBL}$	$V_{CC}$	V

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Total Device Power Dissipation (FR-5 PCB of 1, x 0.75, x 0.062,, $T_A = 25^{\circ}C$ )	P D	150	mW
Derate above 25 $^{\circ}C$		1.2	mW/ $^{\circ}C$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833	$^{\circ}C/W$

**ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}C$  unless otherwise noted)**

Characteristic	Symbol	Min	Typ	Max	Unit
Recommended Operating Supply Voltage	$V_{CC}$	1.8	2.75	10	Volts
Power Supply Current ( $V_{CC} = 2.75 V$ ) $V_{ref}$ , $I_{out}$ are unterminated See Figure 8	$I_{CC}$	—	130	200	mA
Q2 Collector Emitter Breakdown Voltage ( $I_{C2} = 10 \mu A$ , $I_{B2} = 0$ )	$V_{(BR)CEO2}$	15			Volts
Reference Voltage ( $V_{ENBL} = V_{CC} = 2.75 V$ , $V_{out} = 0.7 V$ ) ( $I_{out} = 30 \mu A$ )	$V_{ref}$	2.050	2.075	2.100	Volts
( $I_{out} = 150 \mu A$ ) See Figure 1		2.110	2.135	2.160	
Reference Voltage ( $V_{ENBL} = V_{CC} = 2.75 V$ , $V_{out} = 0.7 V$ , -40 $^{\circ}C \leq T_A \leq +85^{\circ}C$ )					
$V_{CC}$ Pulse Width = 10 mS, Duty Cycle = 1% ( $I_{out} = 10 \mu A$ )	$\Delta V_{ref}$		$\pm 5.0$	$\pm 10$	mV
( $I_{out} = 30 \mu A$ )			$\pm 15$	$\pm 30$	
( $I_{out} = 100 \mu A$ ) See Figures 2 and 11			$\pm 25$	$\pm 50$	



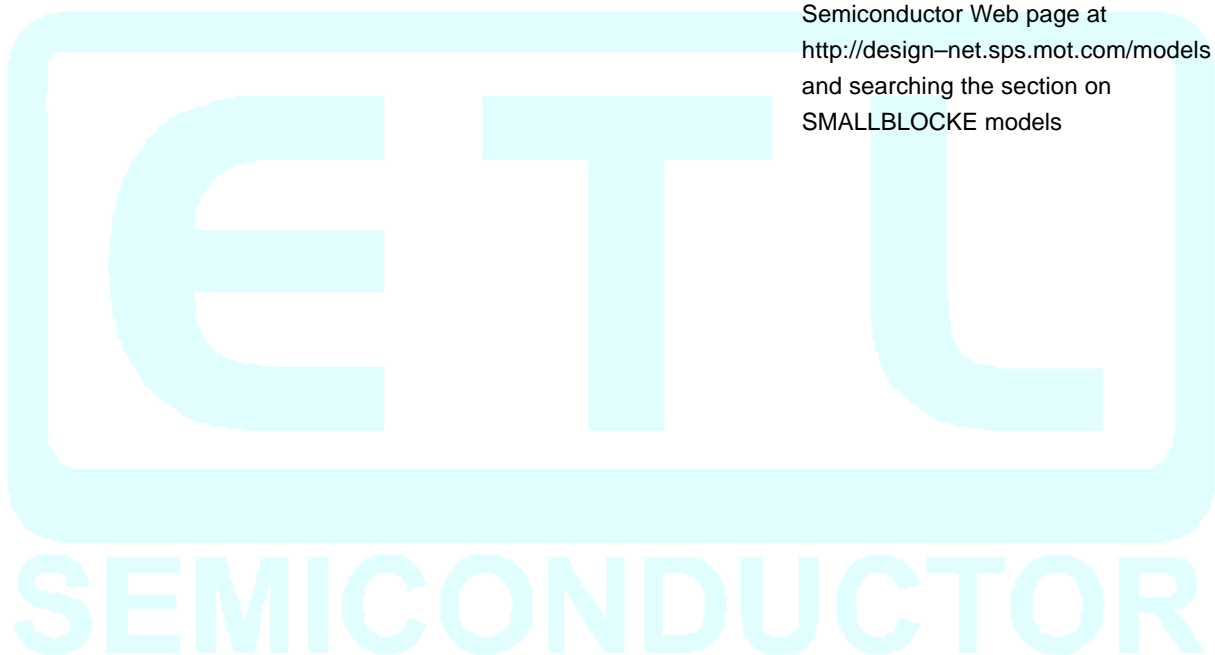
## MDC5001T1

The following SPICE models are provided as a convenience to the user and every effort has been made to insure their accuracy. However, no responsibility for their accuracy is assumed by ON Semiconductor.

<b>.MODEL Q4 NPN</b>		<b>.MODEL Q1, Q2 PNP</b>	
BF = 136	NE = 1.6	BF = 87	NK = 0.5
BR = 0.2	NF = 1.005	BR = 0.6	NR = 1.0
CJC = 318.6 f	RB = 140	CJC = 800E-15	RB = 720
CJE = 569.2 f	RBM = 70	CJE = 46E-15	RBM = 470
CJS = 1.9 p	RC = 180	EG = 1.215	RC = 180
EG = 1.215	RE = 1.6	FC = 0.5	RE = 26
FC = 0.5	TF = 553.6 p	IKF = 3.8E-04	TF = 15E-9
IKF = 24.41 m	TR = 10 n	IKR = 2.0	TR = 50E-09
IKR = 0.25	VAF = 267.6	IRB = 0.9E-3	VAF = 54.93
IRB = 0.0004	VAR = 12	IS = 1.027E-15	VAR = 20
IS = 256E-18	VJC = 0.4172	ISC = 10E-18	VAR = 20
ISC = 1 f	VJE = 0.7245	ISE = 1.8E-15	VJC = 0.4172
ISE = 500E-18	VJS = 0.39	ITF = 2E-3	VJE = 0.4172
ITF = 0.9018	VTF = 10	MJC = 0.2161	VTF = 10
MJC = 0.2161	XTB = 1.5	MJE = 0.2161	XTB = 1.5
MJE = 0.3373	XTF = 2.077	NC = 0.8	XTF = 2.0
MJS = 0.13	XTI = 3	NE = 1.38	XTI = 3
NC = 1.09		NF = 1.015	

<b>RESISTOR VALUES</b>
R <sub>1</sub> = 12 K
R <sub>2</sub> = 6 K
R <sub>3</sub> = 3.4 K
R <sub>4</sub> = 12 K
R <sub>5</sub> = 20 K
R <sub>6</sub> = 40 K

These models can be retrieved electronically by accessing the ON Semiconductor Web page at <http://design-net.sps.mot.com/models> and searching the section on SMALLBLOCKE models



TYPICAL OPEN LOOP CHARACTERISTICS

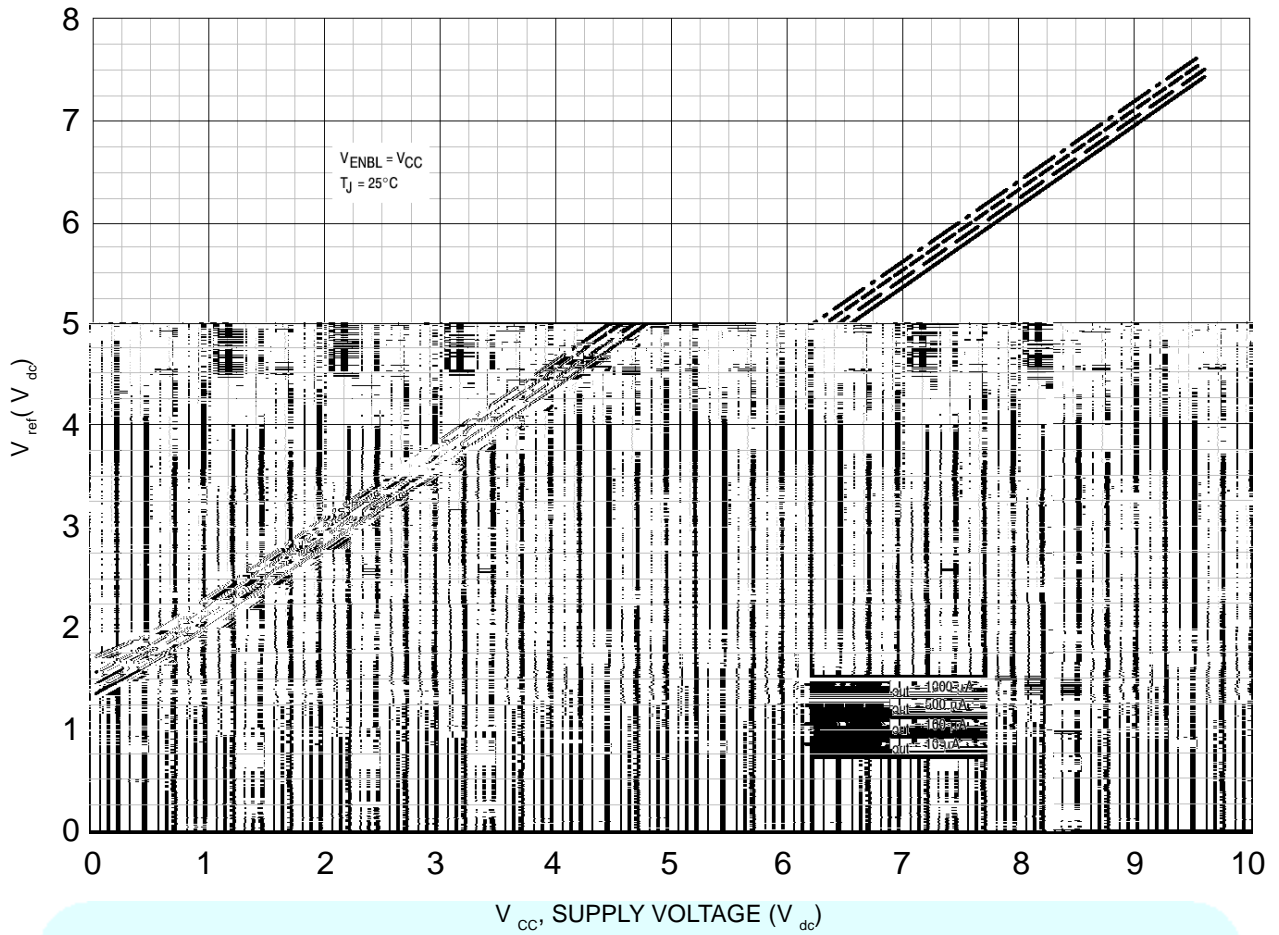
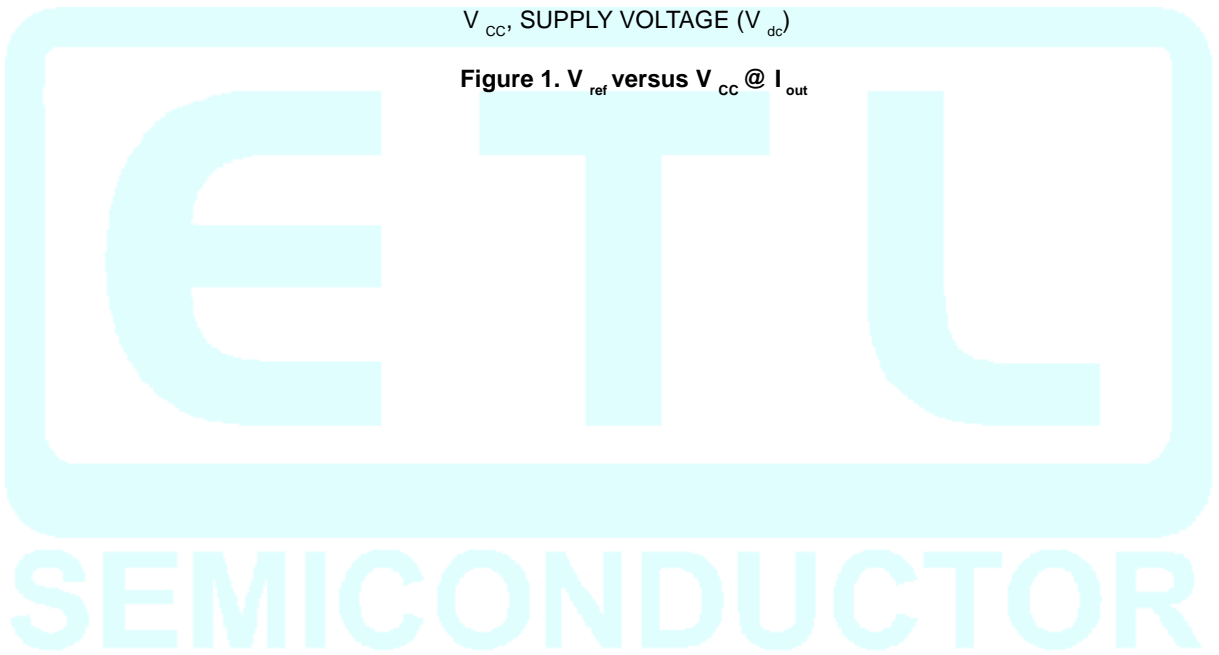


Figure 1.  $V_{ref}$  versus  $V_{CC}$  @  $I_{out}$



**TYPICAL OPEN LOOP CHARACTERISTICS**  
(Refer to Circuits of Figures 10 through 15)

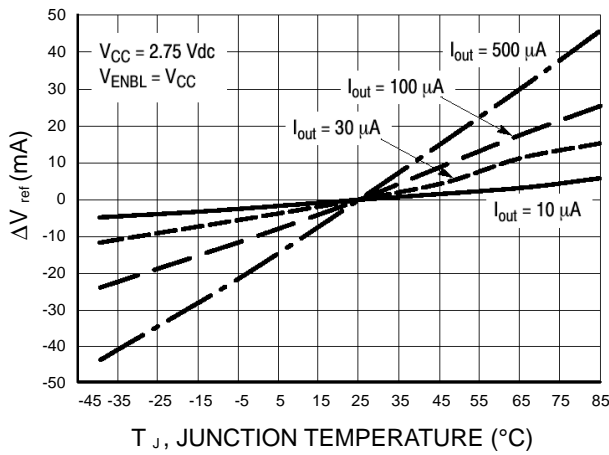


Figure 2.  $\Delta V_{ref}$  versus  $T_J$  @  $I_{out}$

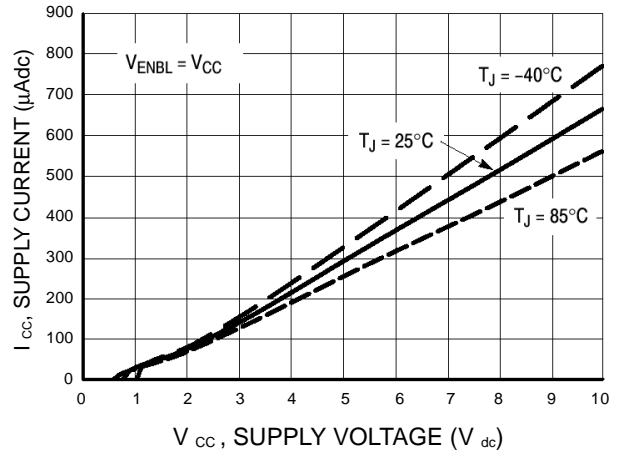


Figure 3.  $I_{CC}$  versus  $V_{CC}$  @  $T_J$

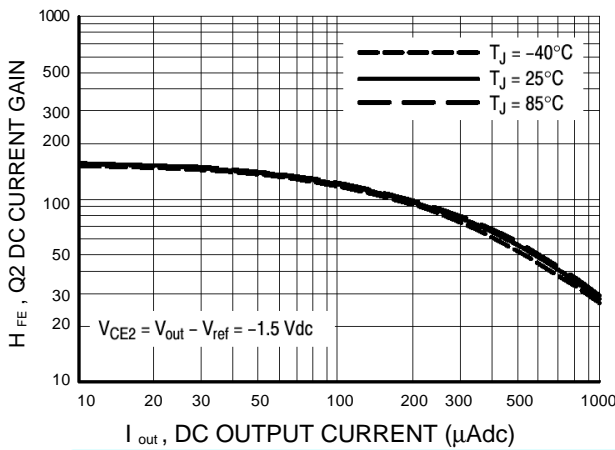


Figure 4. Q2 Current Gain versus Output Current @  $T_J$

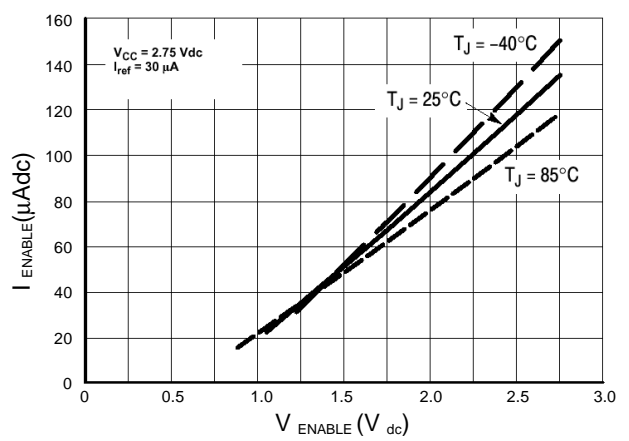


Figure 5.  $I_{enable}$  versus  $V_{enable}$

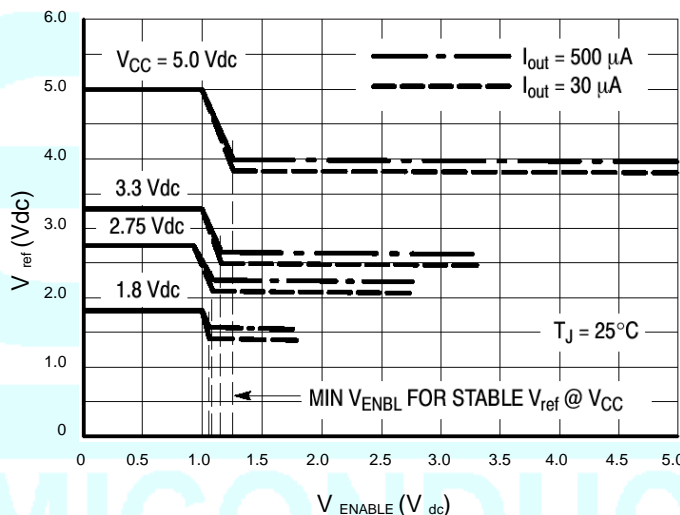
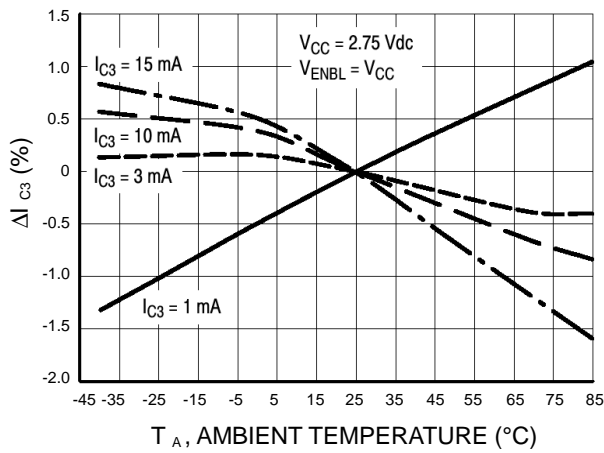


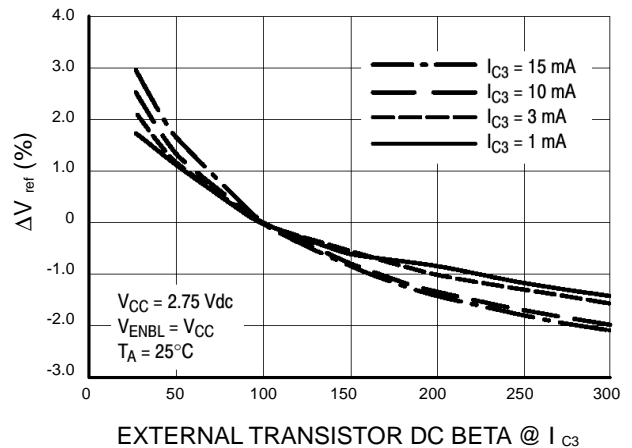
Figure 6.  $V_{ref}$  versus  $V_{enable}$  @  $V_{CC}$  and  $I_{out}$

**TYPICAL CLOSED LOOP PERFORMANCE**

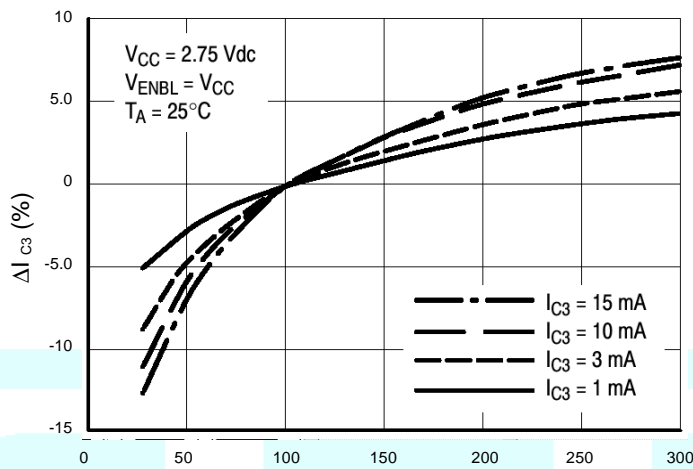
(Refer to Circuits of Figures 16 & 17)



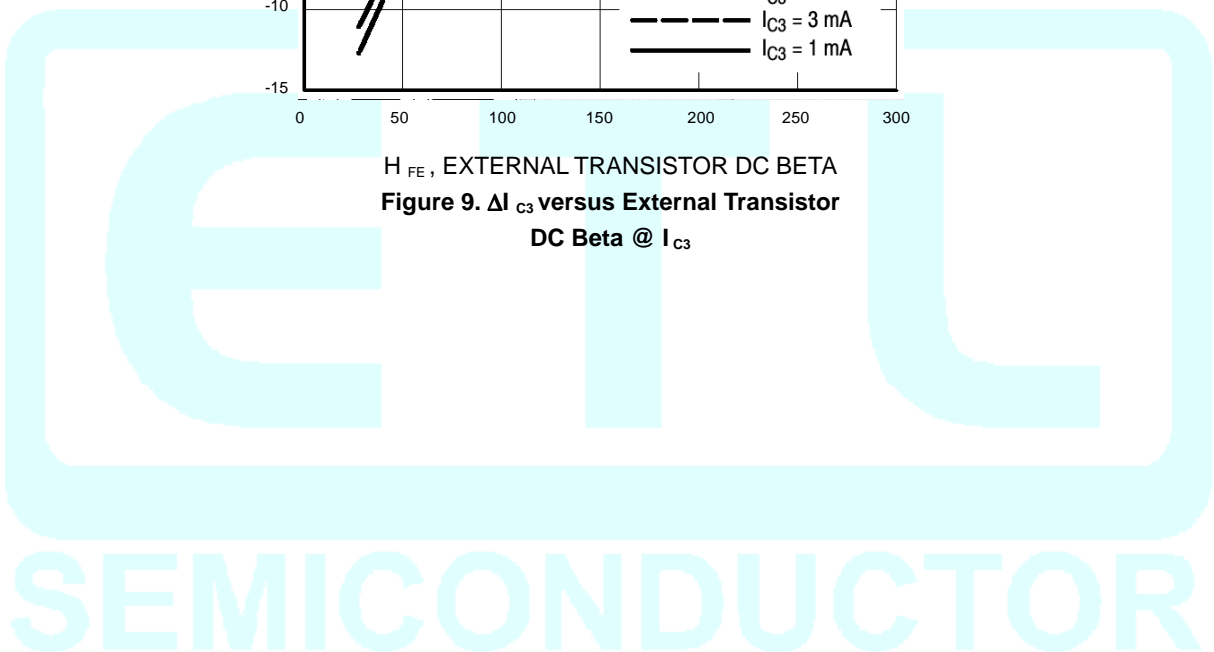
**Figure 7.  $\Delta I_{C3}$  versus  $T_A$  @  $I_{C3}$**



**Figure 8.  $\Delta V_{ref}$  versus External Transistor DC Beta @  $I_{C3}$**



**Figure 9.  $\Delta I_{C3}$  versus External Transistor DC Beta @  $I_{C3}$**



OPEN LOOP TEST CIRCUITS

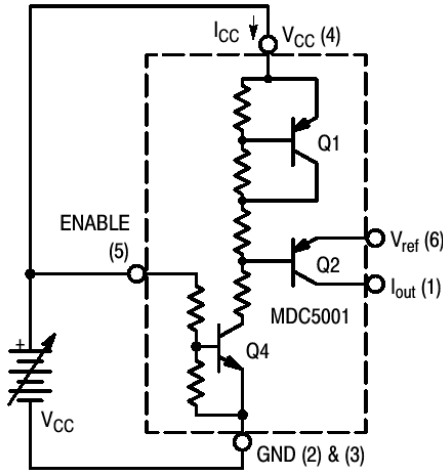


Figure 10. I<sub>cc</sub> versus V<sub>cc</sub> Test Circuit

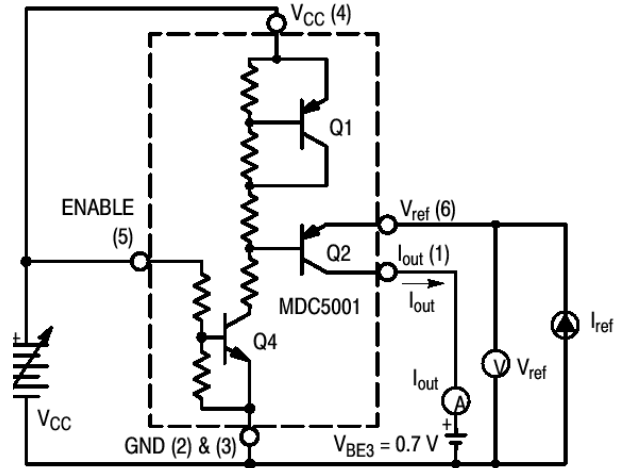


Figure 11. V<sub>ref</sub> versus V<sub>cc</sub> Test Circuit

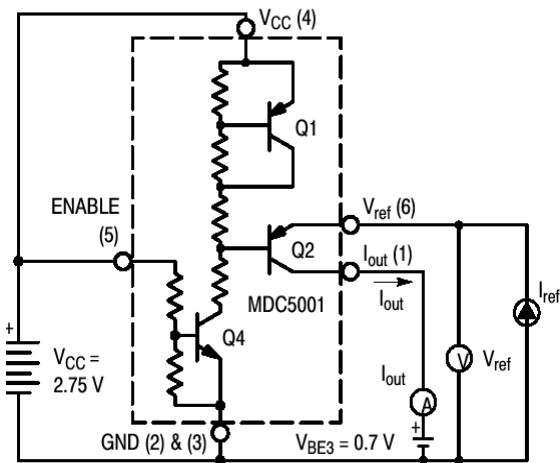


Figure 12. V<sub>ref</sub> versus T<sub>J</sub> Test Circuit

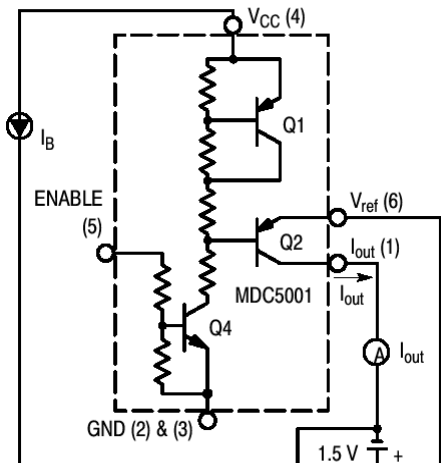


Figure 13. H<sub>FE</sub> versus I<sub>out</sub> Test Circuit

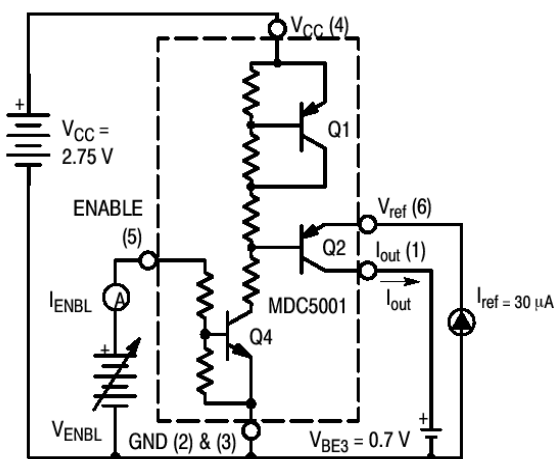


Figure 14. I<sub>ENBL</sub> versus V<sub>ENBL</sub> Test Circuit

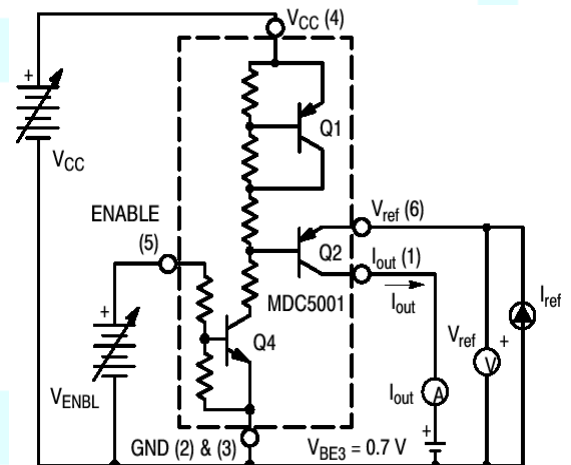


Figure 15. V<sub>ref</sub> versus V<sub>ENBL</sub> Test Circuit

NOTE 1: V<sub>BE3</sub> is used to simulate actual operating conditions that reduce V<sub>CE2</sub> & H<sub>FE2</sub>, and increase I<sub>B2</sub> & V<sub>ref</sub>.

CLOSED LOOP TEST CIRCUITS

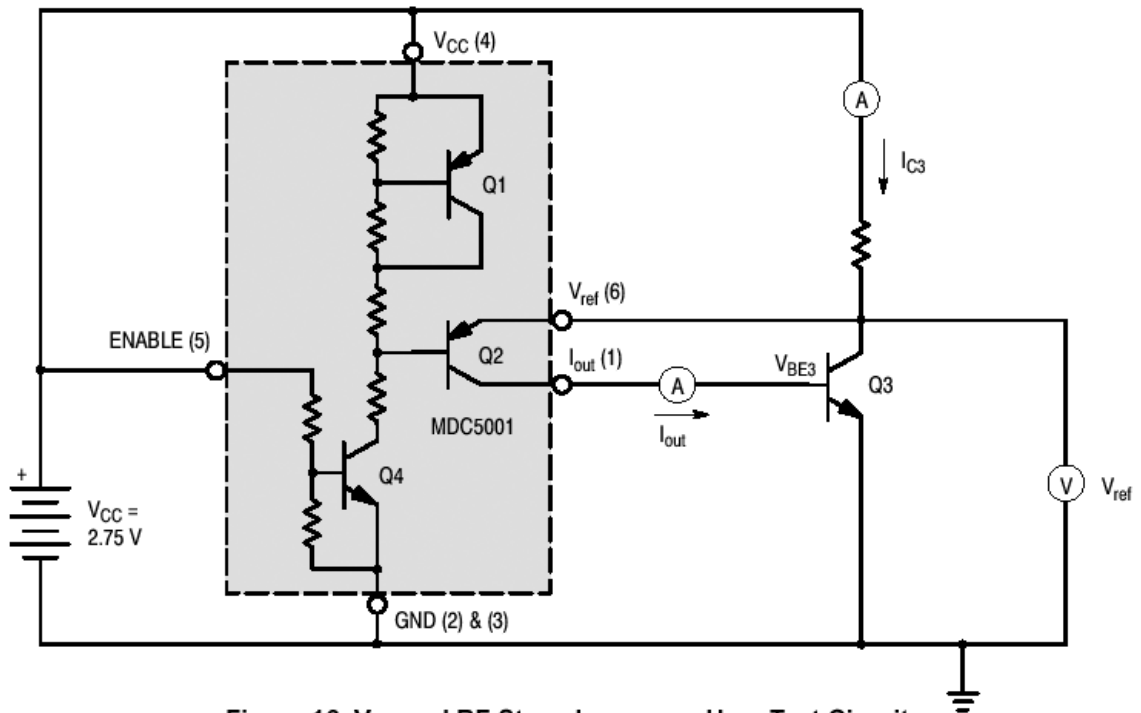
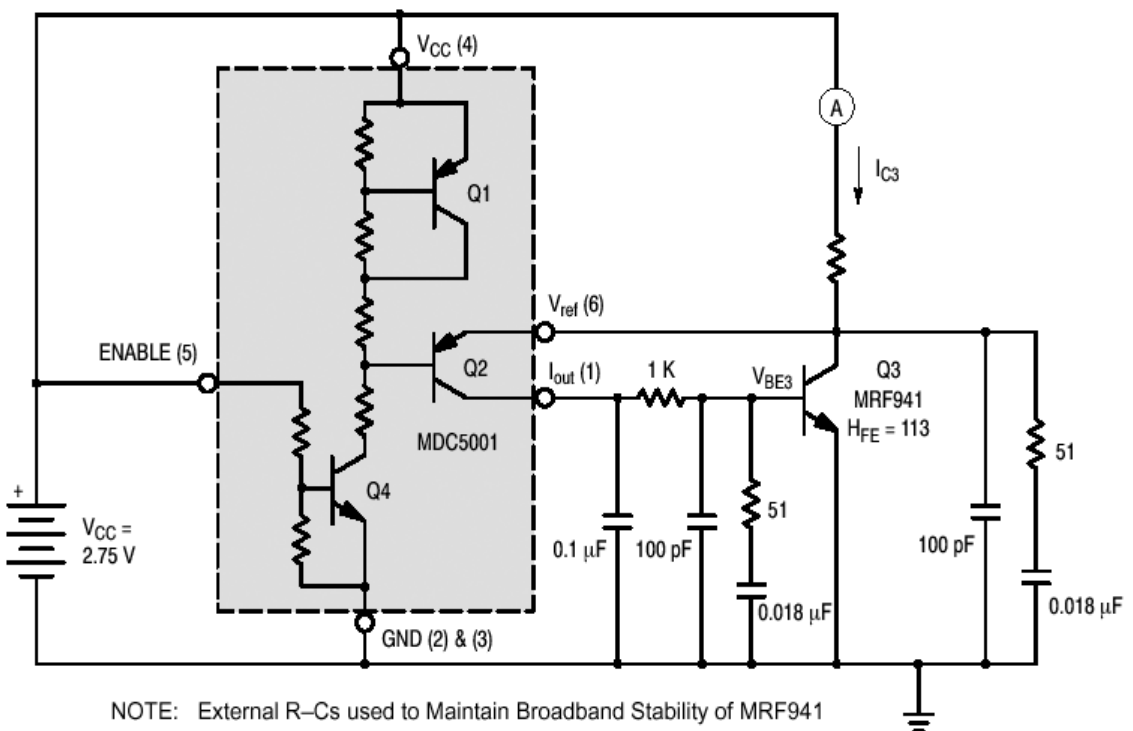


Figure 16.  $V_{ref}$  and RF Stage  $I_{c3}$  versus  $H_{FE3}$  Test Circuit

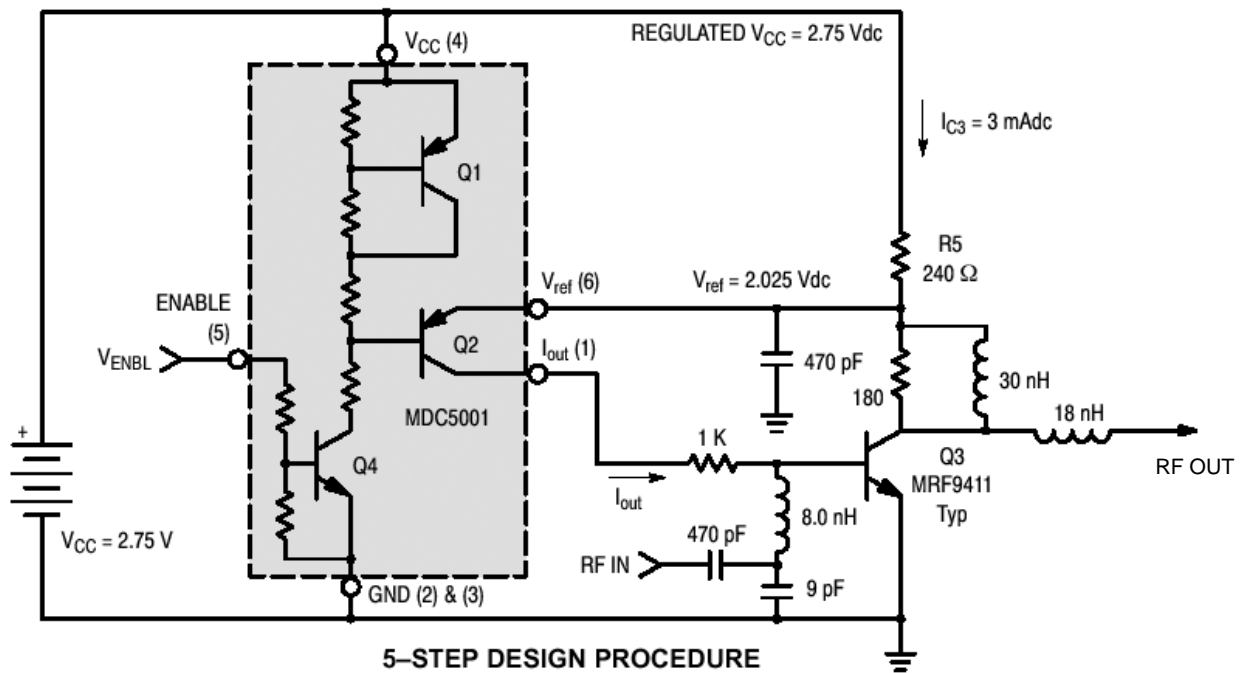


NOTE: External R-Cs used to Maintain Broadband Stability of MRF941

Figure 17. RF Stage  $I_{c3}$  versus  $T_A$  Test Circuit

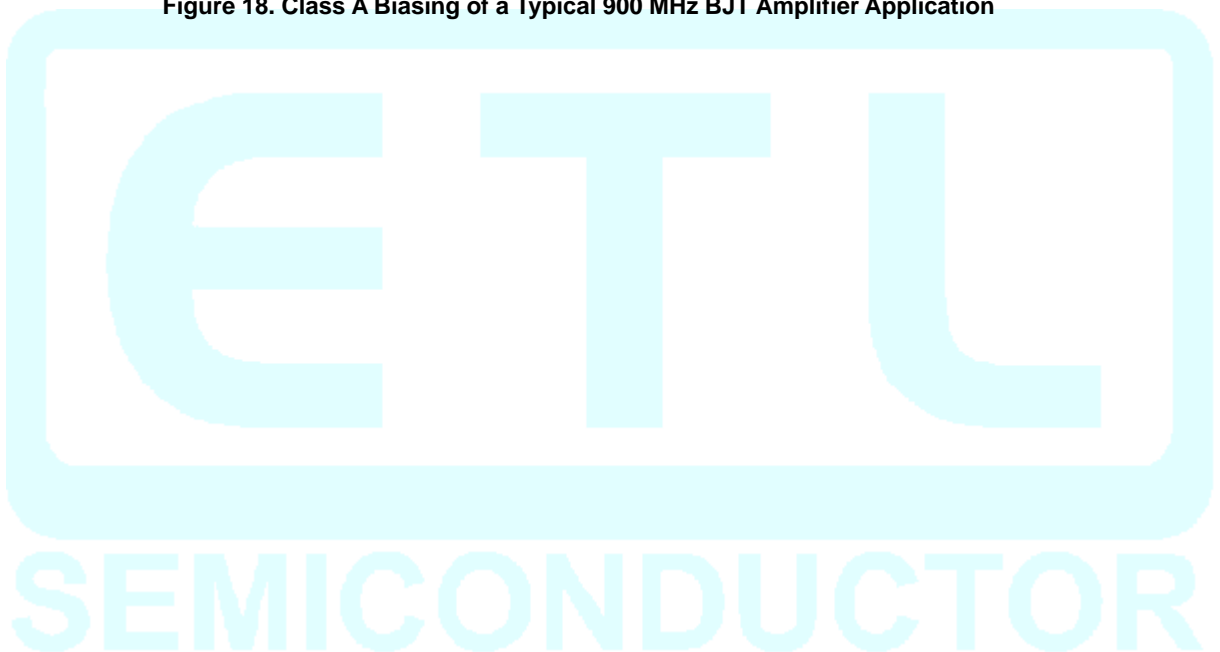


APPLICATION CIRCUITS

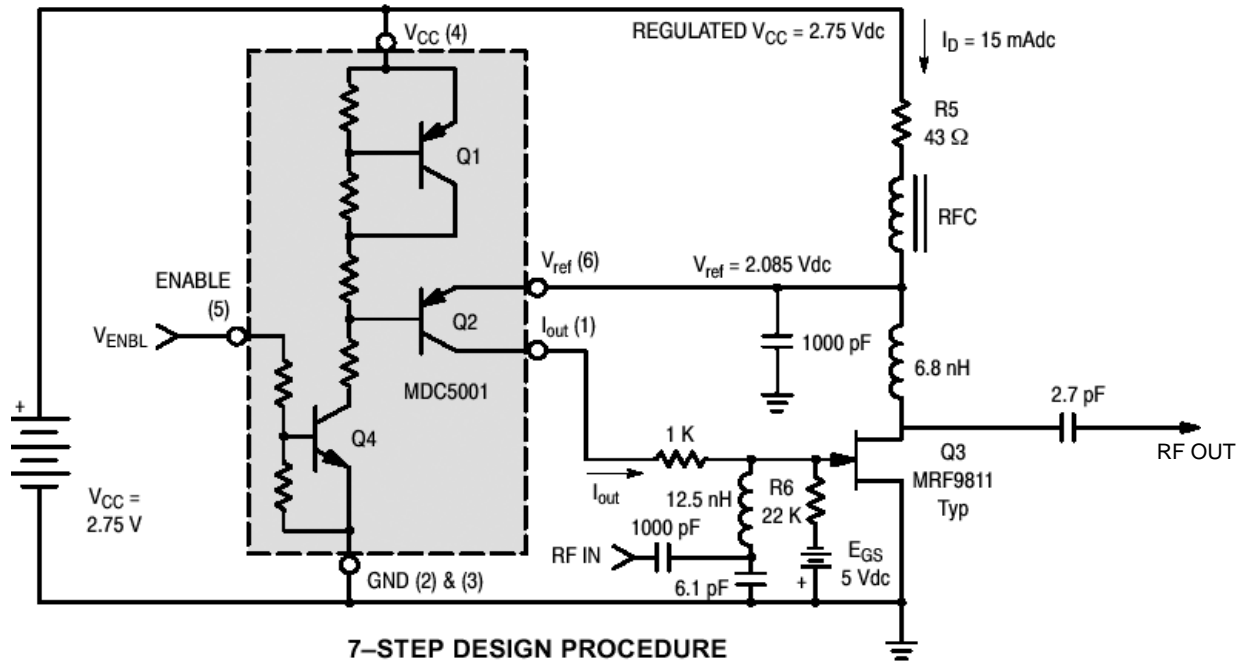


- Step 1: Choose V<sub>CC</sub> (1.8 V Min to 10 V Max)
- Step 2: Insure that Min V<sub>ENBL</sub> is . minimum indicated in Figures 5 and 6.
- Step 3: Choose bias current, I<sub>C3</sub> , and calculate needed I<sub>out</sub> from typ H FE3
- Step 4: From Figure 1, read V<sub>ref</sub> for V<sub>CC</sub> and I<sub>out</sub> calculated.
- Step 5: Calculate Nominal R<sub>5</sub> =  $(V_{CC} - V_{ref}) \div (I_{C3} + I_{out})$ . Tweak as desired.

**Figure 18. Class A Biasing of a Typical 900 MHz BJT Amplifier Application**



APPLICATION CIRCUITS



7-STEP DESIGN PROCEDURE

- Step 1: Choose  $V_{CC}$  (1.8 V Min to 10 V Max)
- Step 2: Insure that Min  $V_{ENBL}$  is  $\geq$  minimum indicated in Figures 5 and 6.
- Step 3: Choose bias current,  $I_D$ , and determine needed gate-source voltage,  $V_{GS}$ .
- Step 4: Choose  $I_{out}$  keeping in mind that too large an  $I_{out}$  can impair MDC5000  $\Delta V_{ref}/\Delta T_J$  performance (Figure 2) but too large an  $R_6$  can cause  $I_{DGO}$  &  $I_{GSO}$  to bias on the FET.
- Step 5: Calculate  $R_6 = (V_{GS} + E_{GS}) \div I_{out}$
- Step 6: From Figure 1, read  $V_{ref}$  for  $V_{CC}$  &  $I_{out}$  chosen
- Step 7: Calculate Nominal  $R_5 = (V_{CC} - V_{ref}) \div (I_D + I_{out})$ . Tweak as desired.

Figure 19. Class A Biasing of a Typical 890 MHz Depletion Mode GaAs FET Amplifier

